

MOSFET - Power, Single N-Channel, STD Gate, SO8FL

40 V, 0.6 mΩ, 384 A

NVMFWS0D63N04XM

MAXIMUM RATINGS (T_J = 25°C unless otherwise stated)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V _{DSS}	40	V
Gate-to-Source Voltage	V _{GS}	±20	V
Continuous Drain Current	I _D	T _C = 25°C	384
		T _C = 100°C	271
Power Dissipation	P _D	157	W
Continuous Drain Current R _{θJA}	I _D	T _C = 25°C	60
		T _C = 100°C	42
Pulsed Drain Current	I _{DM}	900	A
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 to 175	°C
Source Current (Body Diode)	I _S	131	A
Single Pulse Avalanche Energy	E _{AS}	585	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T _L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

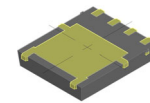
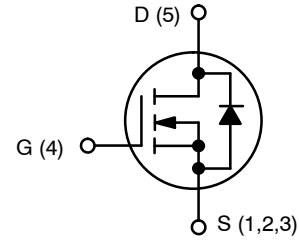
THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case (Note 2)	R _{θJC}	0.95	°C/W
Thermal Resistance, Junction-to-Ambient (Notes 1, 2)	R _{θJA}	39	

- Surface mounted on FR4 board using 650 mm², 2 oz Cu pad.
- The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.

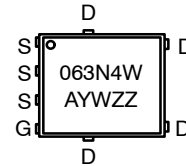
V _{(BR)DSS}	R _{DS(on)} MAX	I _D MAX
40 V	0.6 mΩ @ V _{GS} = 10 V	384 A

N-CHANNEL MOSFET



DFNW5 (SO-8FL)
CASE 507BA

MARKING DIAGRAM



063N4W = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 5 of this data sheet.

NVMFWS0D63N04XM

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 1 mA, T _J = 25°C	40			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	ΔV _{(BR)DSS} /ΔT _J	I _D = 1 mA, Referenced to 25°C		15		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 40 V, T _J = 25°C			10	μA
		V _{DS} = 40 V, T _J = 125°C			100	
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} = 20 V, V _{DS} = 0 V			100	nA

ON CHARACTERISTICS

Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 10 V, I _D = 30 A, T _J = 25°C		0.54	0.6	mΩ
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 230 μA, T _J = 25°C	2.5		3.5	V
Gate Threshold Voltage Temperature Coefficient	ΔV _{GS(TH)} /ΔT _J	V _{GS} = V _{DS} , I _D = 230 μA		-7.24		mV/°C
Forward Trans-conductance	g _{FS}	V _{DS} = 5 V, I _D = 30 A		174		S

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C _{ISS}	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz		5862		pF
Output Capacitance	C _{OSS}			3760		
Reverse Transfer Capacitance	C _{RSS}			50		
Total Gate Charge	Q _{G(TOT)}	V _{DD} = 32 V, I _D = 50 A, V _{GS} = 10 V		92.2		nC
Threshold Gate Charge	Q _{G(TH)}			17.2		
Gate-to-Source Charge	Q _{GS}			25.8		
Gate-to-Drain Charge	Q _{GD}			17.4		
Gate Resistance	R _G	f = 1 MHz		0.60		Ω

SWITCHING CHARACTERISTICS

Turn-On Delay Time	t _{d(ON)}	Resistive Load, V _{GS} = 0/10 V, V _{DD} = 32 V, I _D = 50 A, R _G = 0 Ω		28		ns
Rise Time	t _r			9		
Turn-Off Delay Time	t _{d(OFF)}			47		
Fall Time	t _f			7.3		

SOURCE TO DRAIN DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	I _S = 30 A, V _{GS} = 0 V, T _J = 25°C		0.78		V
		I _S = 30 A, V _{GS} = 0 V, T _J = 125°C		0.63		
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, I _S = 50 A, di/dt = 100 A/μs, V _{DD} = 32 V		83		ns
Charge Time	t _a			47		
Discharge Time	t _b			36		
Reverse Recovery Charge	Q _{RR}			246		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

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TYPICAL CHARACTERISTICS

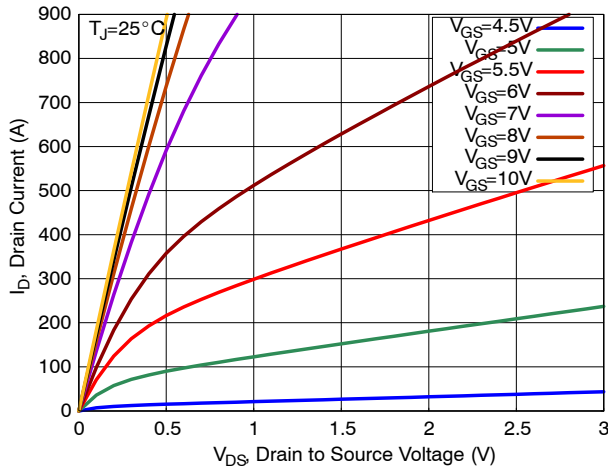


Figure 1. On-Region Characteristics

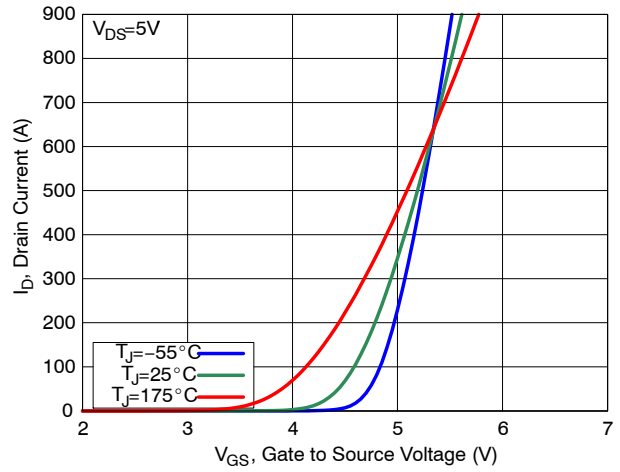


Figure 2. Transfer Characteristics

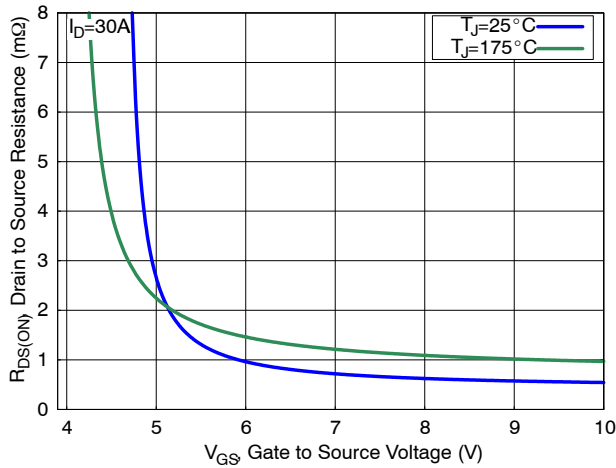


Figure 3. On-Resistance vs. Gate Voltage

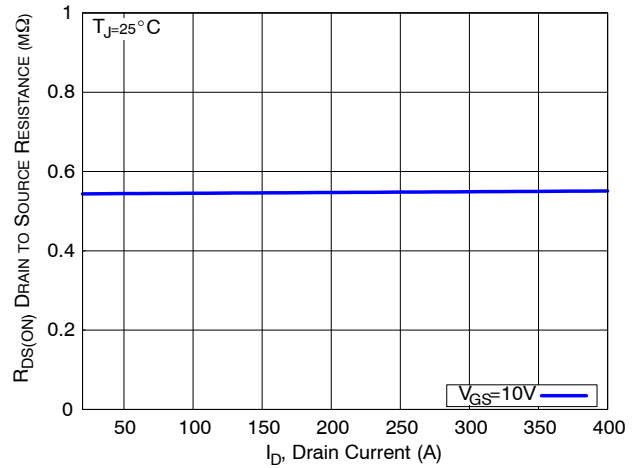


Figure 4. On-Resistance vs. Drain Current

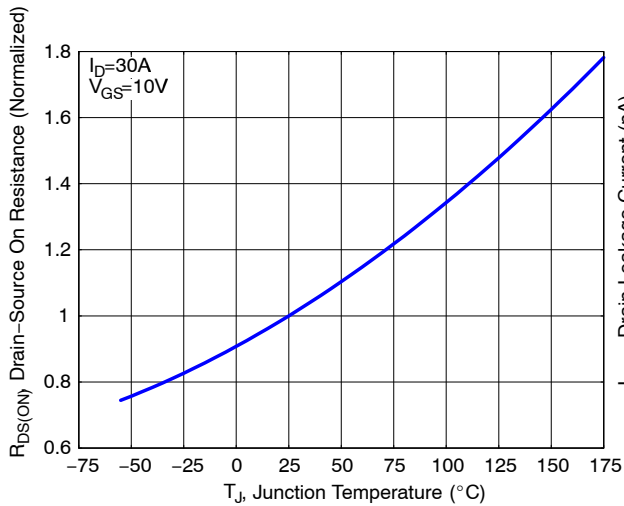


Figure 5. Normalized On-Resistance vs. Junction Temperature

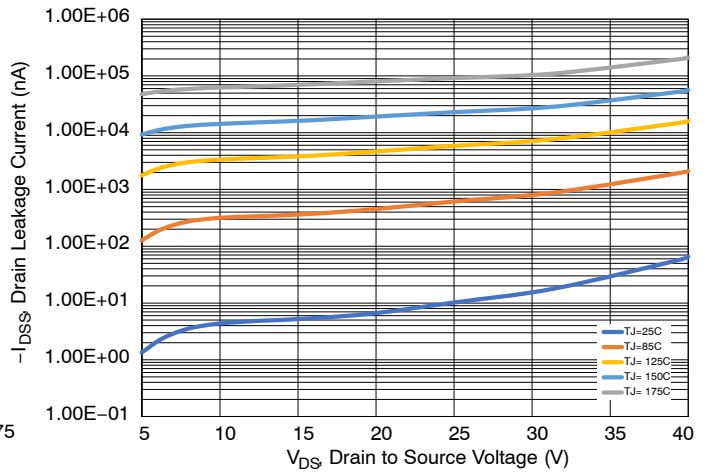


Figure 6. Drain-to-Source Leakage Current vs. Drain Voltage

NVMFWS0D63N04XM

TYPICAL CHARACTERISTICS (continued)

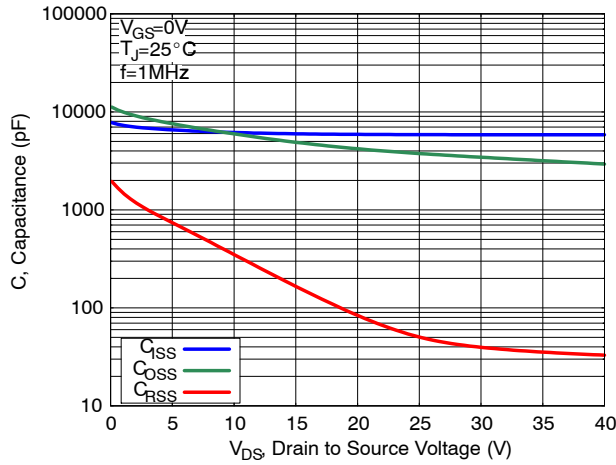


Figure 7. Capacitance Characteristics

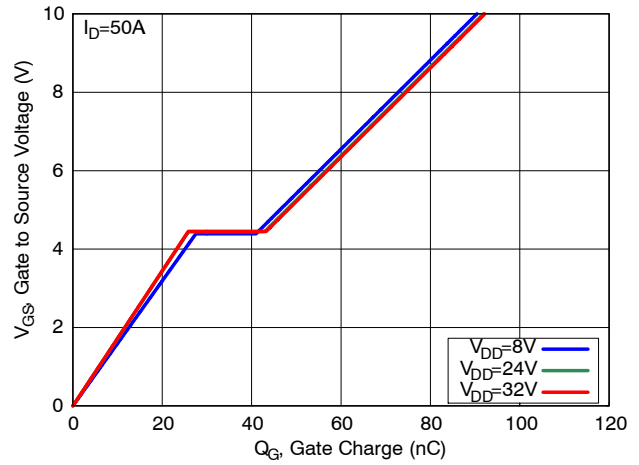


Figure 8. Gate Charge Characteristics

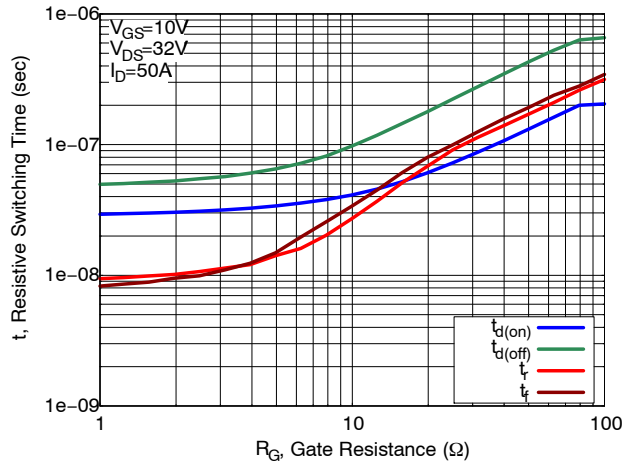


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

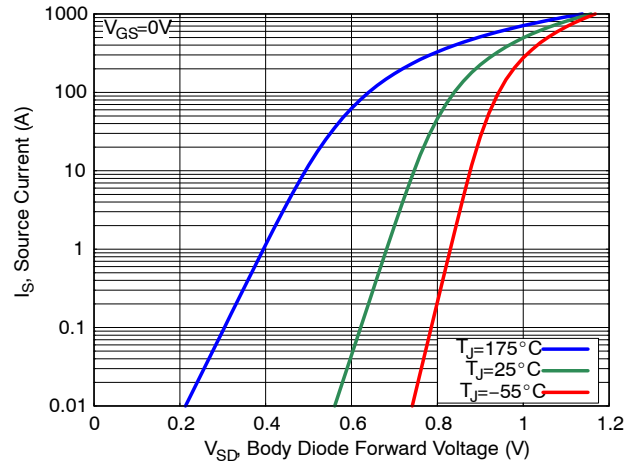


Figure 10. Diode Forward Voltage vs. Current

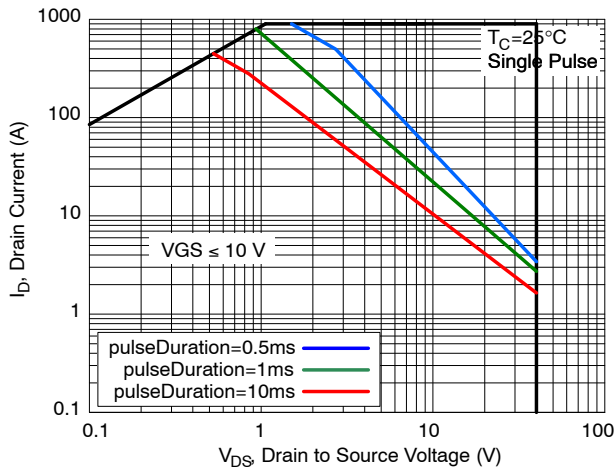


Figure 11. Safe Operating Area (SOA)

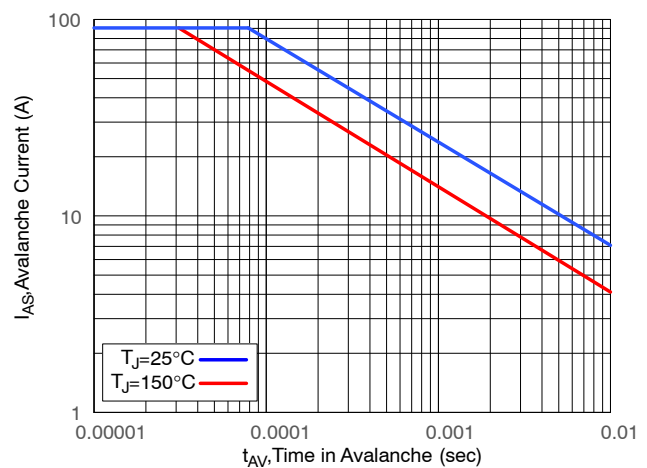


Figure 12. Avalanche Current vs. Pulse Time (UIS)

NVMFWS0D63N04XM

TYPICAL CHARACTERISTICS (continued)

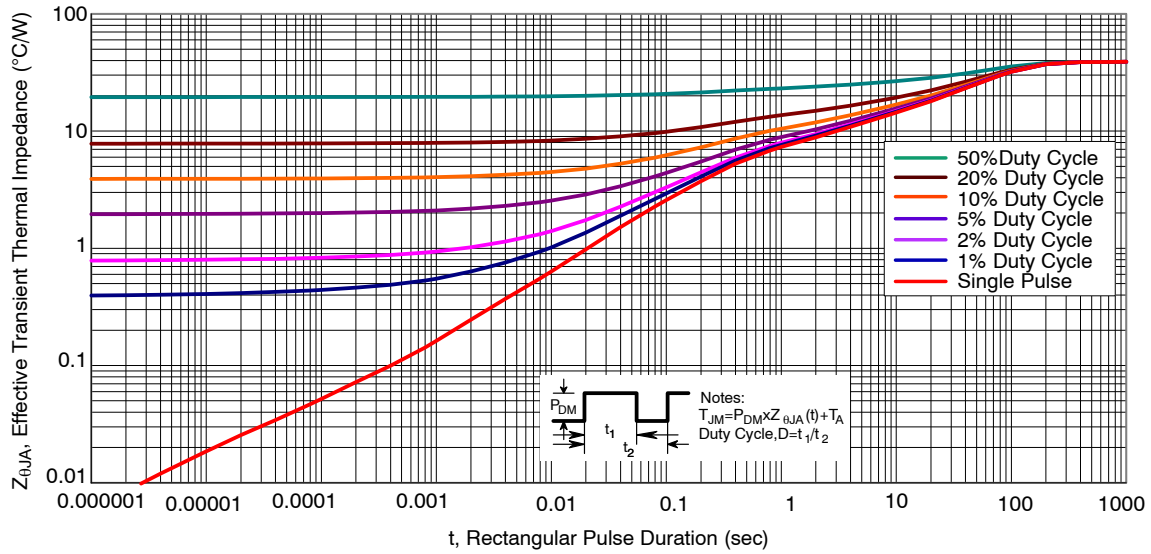


Figure 13. Thermal Characteristics

ORDERING INFORMATION

Device	Marking	Package	Shipping†
NVMFWS0D63N04XMT1G	063N4W	DFNW5 (Pb-Free)	1500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

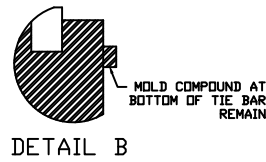
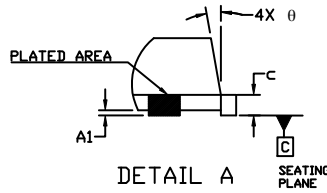
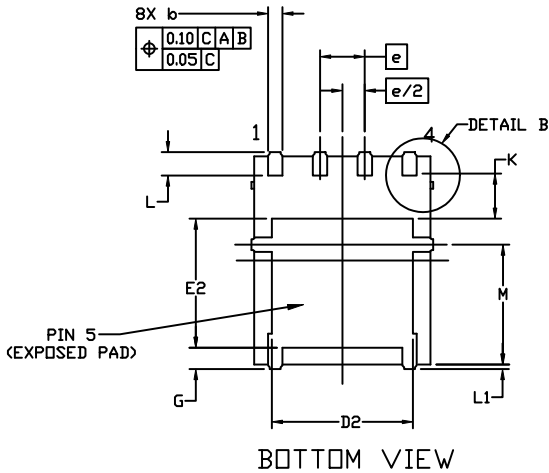
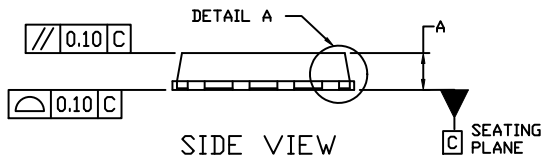
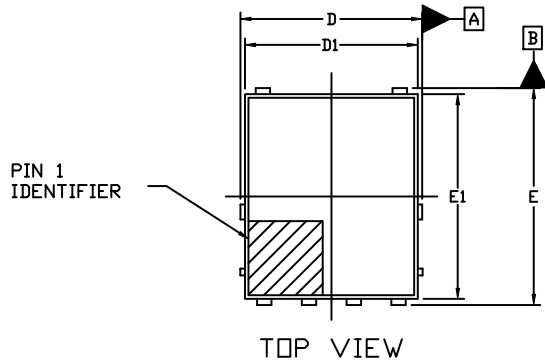
NVMFWS0D63N04XM

PACKAGE DIMENSIONS

DFNW5 5x6 (FULL-CUT SO8FL WF)

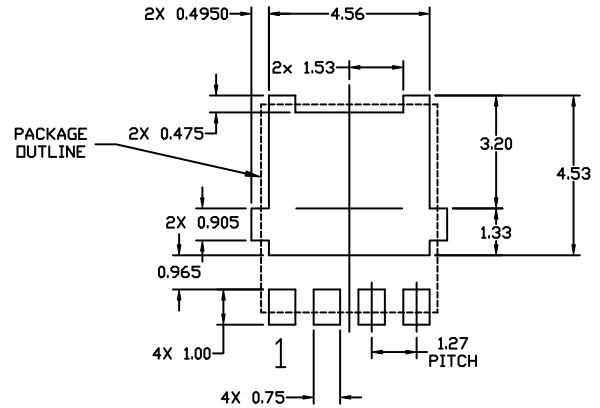
CASE 507BA

ISSUE A



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
 2. CONTROLLING DIMENSION: MILLIMETERS
 3. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
 4. THIS PACKAGE CONTAINS WETTABLE FLANK DESIGN FEATURES TO AID IN FILLET FORMATION ON THE LEADS DURING MOUNTING.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0.00	---	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
e	1.27 BSC		
G	0.51	0.575	0.71
K	1.20	1.35	1.50
L	0.51	0.575	0.71
L1	0.150 REF		
M	3.00	3.40	3.80
θ	0°	---	12°



RECOMMENDED MOUNTING FOOTPRINT

- * For additional information on our Pb-Free strategy and soldering details, please download the [DN Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D](#).

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